

Supplementary Files

Nonvolatile modulation of electronic structure and correlative magnetism of L1₀-FePt films using significant strain induced by shape memory substrates

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Figure S1

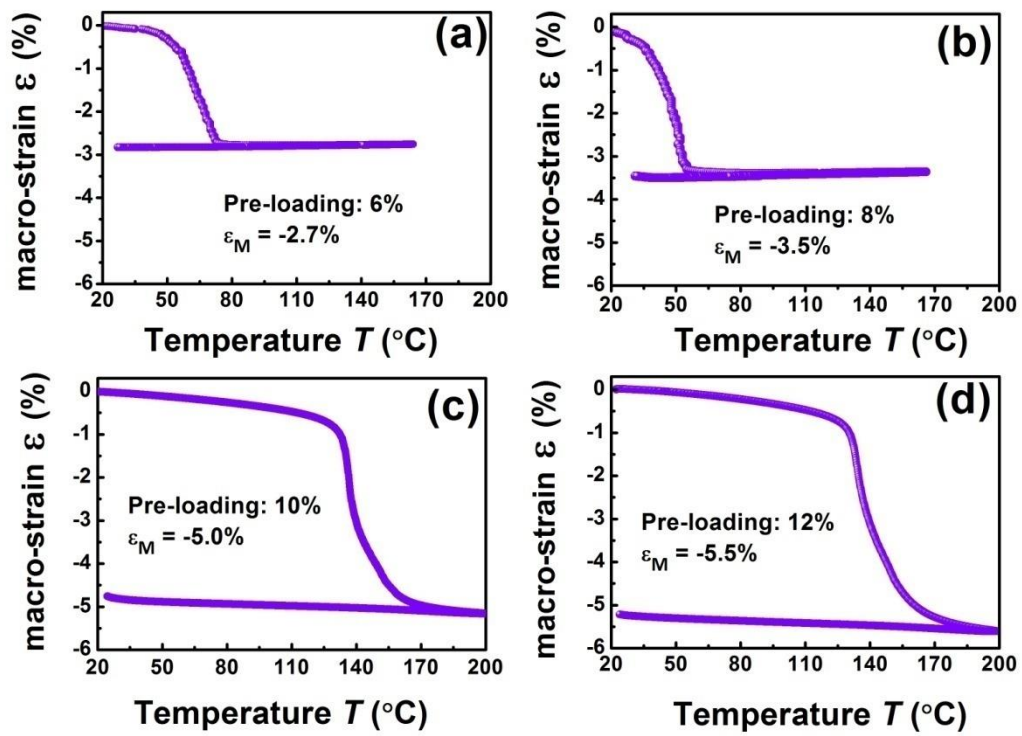


Figure S1 Dynamic thermomechanical analysis (DMA) curves of the pure SMA substrates. (a) Pre-loading 6%, recoverable macro-strain $\epsilon_M = -2.7\%$; (b) Pre-loading 8%, $\epsilon_M = -3.5\%$; (c) Pre-loading 10%, $\epsilon_M = -5.0\%$; (d) Pre-loading 12%, $\epsilon_M = -5.5\%$.

Figure S2

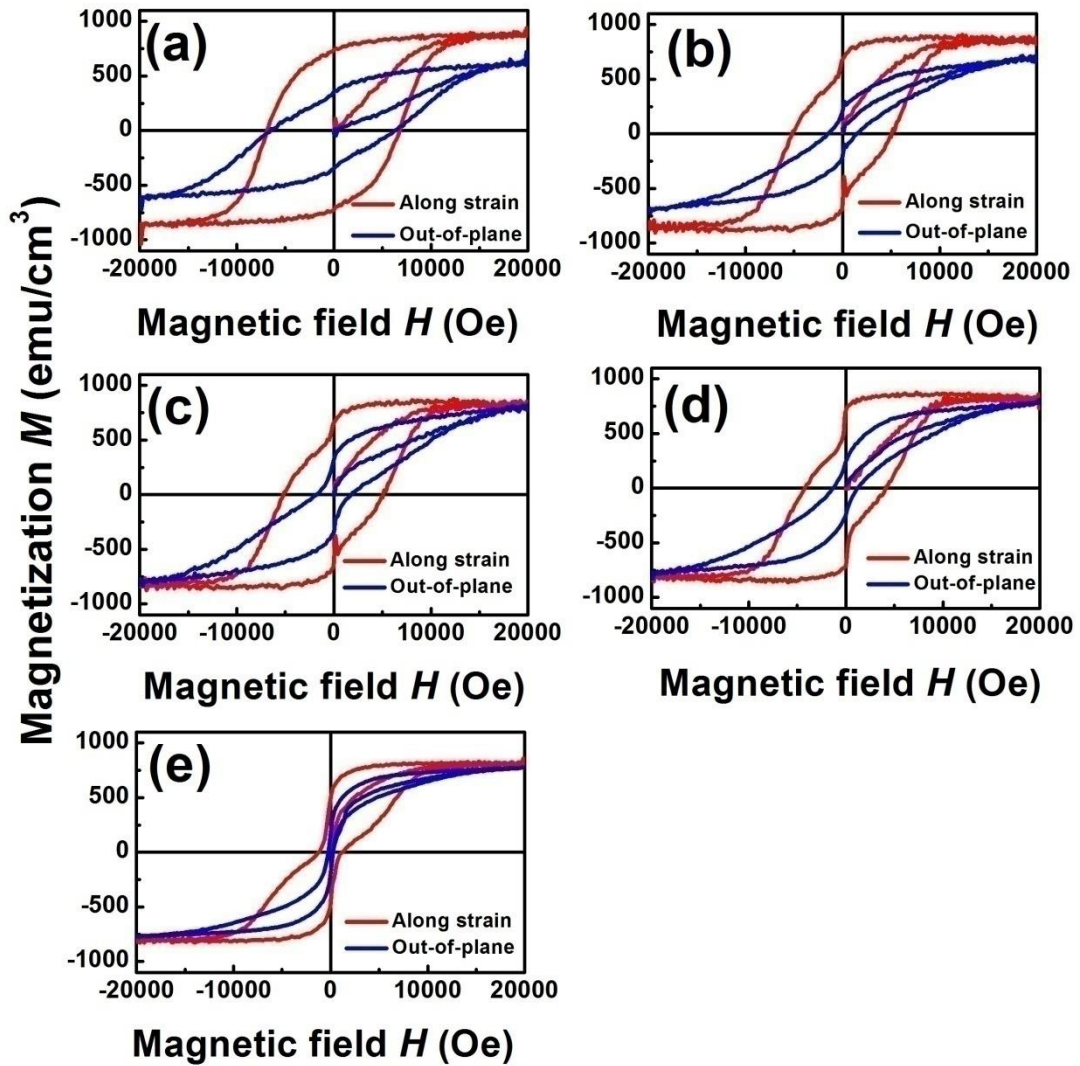


Figure S2 In-plane (along the strain) and out-of-plane hysteresis loops of the lattice strain treated

L1₀-FePt(10 nm) film. (a) $\epsilon_L = 0\%$; (b) $\epsilon_L = -0.48\%$; (c) $\epsilon_L = -0.78\%$; (d) $\epsilon_L = -1.63\%$; (e) $\epsilon_L = -2.18\%$.

Figure S3

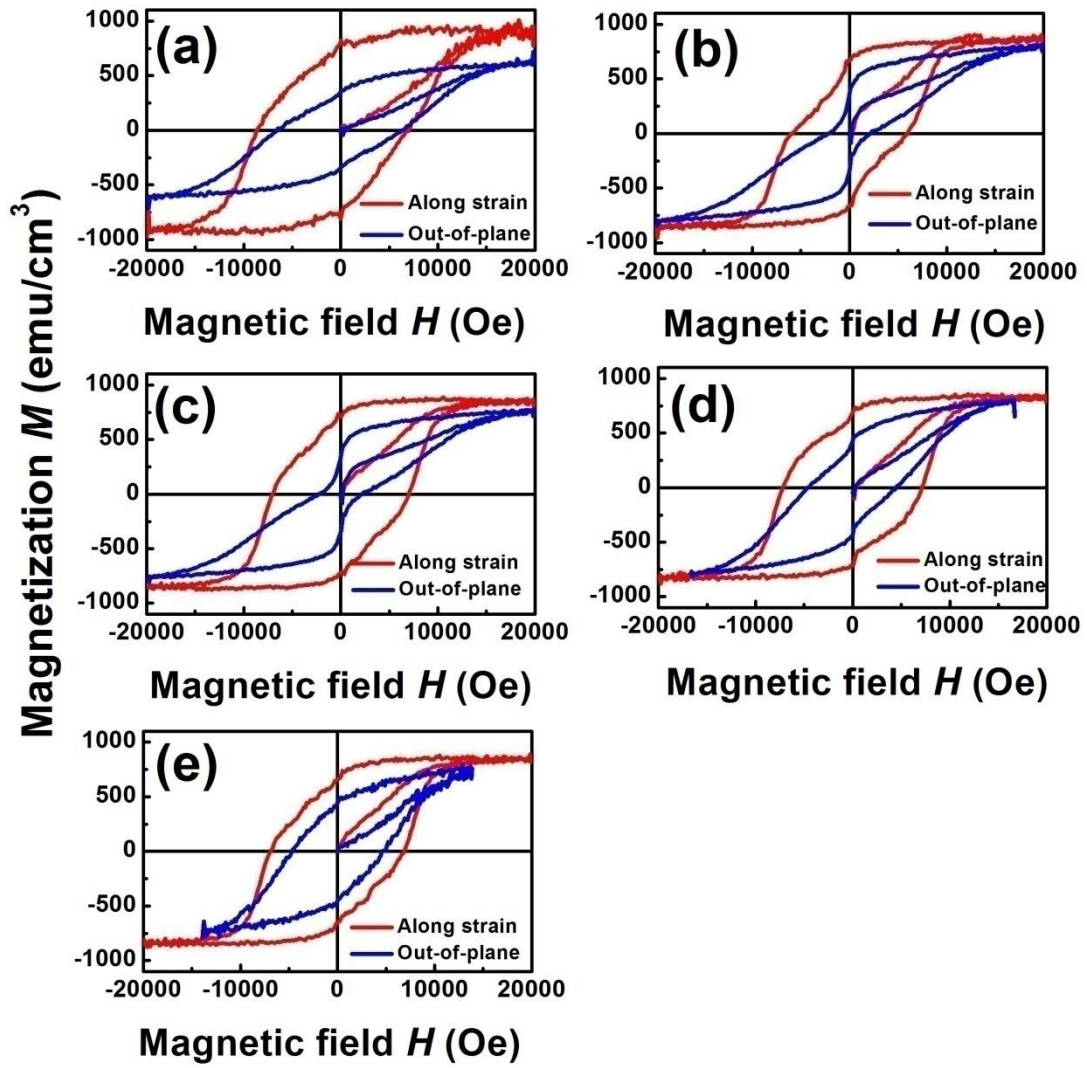


Figure S3 In-plane (along the strain) and out-of-plane hysteresis loops of the lattice strain treated

$L1_0$ -FePt(15 nm) film. (a) $\epsilon_L = 0\%$; (b) $\epsilon_L = -0.48\%$; (c) $\epsilon_L = -0.78\%$; (d) $\epsilon_L = -1.63\%$; (e) $\epsilon_L = -2.18\%$.

Figure S4

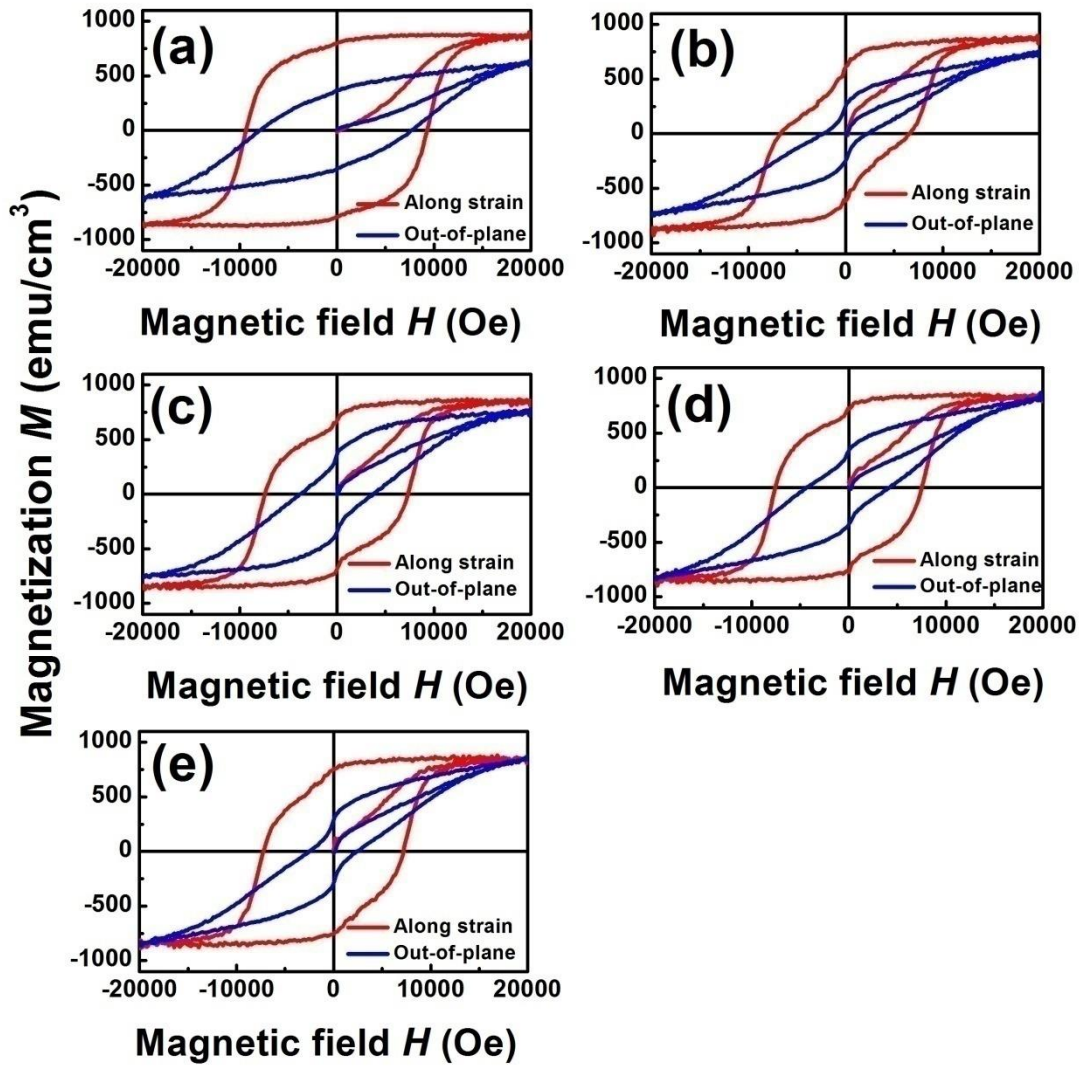


Figure S4 In-plane (along the strain) and out-of-plane hysteresis loops of the lattice strain treated

$\text{L1}_0\text{-FePt}(20 \text{ nm})$ film. (a) $\epsilon_L = 0\%$; (b) $\epsilon_L = -0.48\%$; (c) $\epsilon_L = -0.78\%$; (d) $\epsilon_L = -1.63\%$; (e) $\epsilon_L =$

-2.18% .

Figure S5

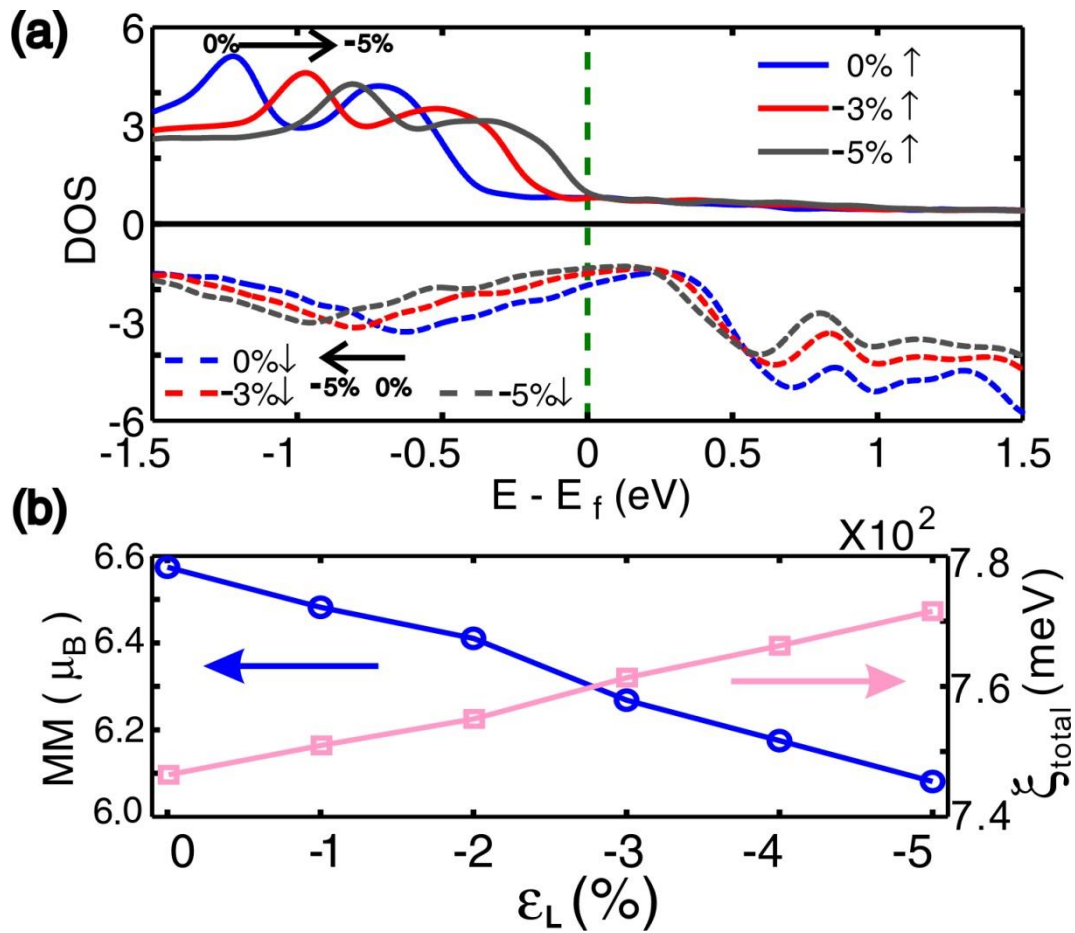


Figure S5 First-principles calculation results for larger strains ranging from 0% to 5%. (a) DOS of spin-up (\uparrow) and spin-down (\downarrow) electrons in L1₀-FePt films, the dashed line stands for Fermi level. When $\epsilon_L = -5\%$, the spin distribution shift by 0.5eV comparing with the $\epsilon_L = 0\%$ case. (b) Variations of magnetic moment (MM) and total SOC strength (ξ_{total}) with ϵ_L . The ξ_{total} increases from 746 meV ($\epsilon_L = 0\%$) to 769 meV ($\epsilon_L = -5\%$) with a considerable variation of 23 meV.

Figure S6

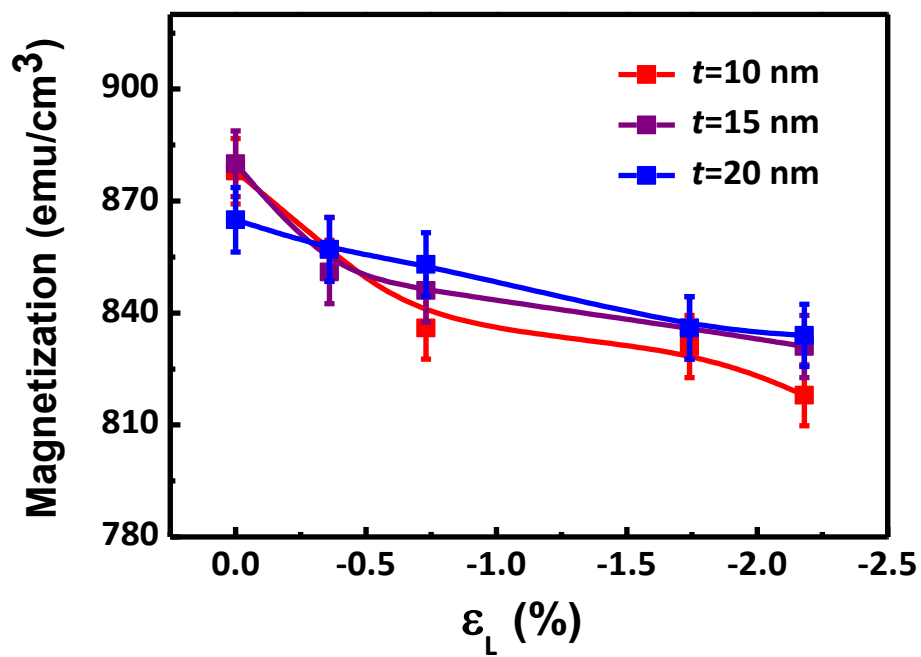


Figure S6 Variations of experimental magnetization in strain treated L1₀-FePt films with ϵ_L .

t represents the thickness of the L1₀-FePt layer.